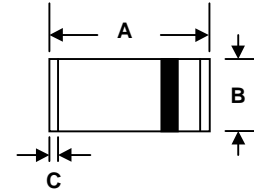


VOLTAGE RANGE: 20 - 40V
CURRENT: 1.0 A

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O



MiniMELF		
Dim	Min	Max
A	3.30	3.60
B	1.40	1.50
C	0.25	0.33
All Dimensions in mm		

Mechanical Data

- Case: LL41(DO-213AB)
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	SM5817	SM5818	SM5819	Unit
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	20	30	40	V
Maximum RMS Voltage	V _{RMS}	14	21	28	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	V
Maximum Average Forward Rectified Current @T _A =75 °C	I _(AV)	1.0			A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load(JEDEC Method)	I _{FSM}	40			A
Maximum Forward Voltage at 1.0A DC	V _F	0.450	0.550	0.600	V
Maximum Forward Voltage at 3.0A DC	V _F	0.750	0.875	0.900	V
Maximum DC Reverse Current @T _J =25°C at Rated DC Bolcking Voltage @T _J =100°C	I _R	1.0 10			mA
Typical Junction Capacitance (Note1)	C _J	110			pF
Typical Thermal Resistance (Note2)	R _{JA}	80			°C/W
Operating Temperature Range	T _J	-55 to +150			°C
Storage Temperature Range	T _{STG}	-55 to +150			°C

NOTES: 1.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC
 2.Thermal resistance junction to ambient,

FIG. 1 - FORWARD CURRENT DERATING CURVE

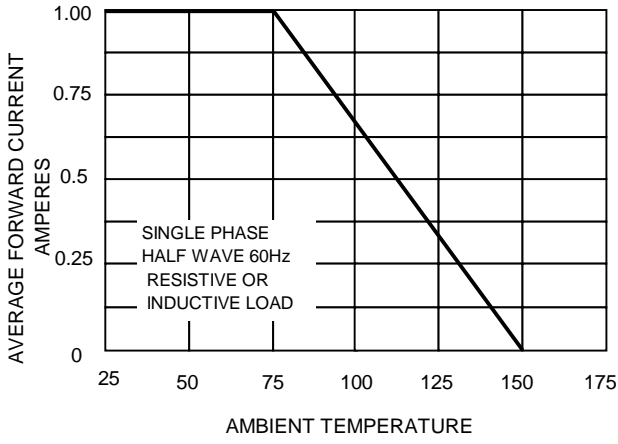


FIG. 2 - MAXIMUM NON-REPETITIVE SURGE CURRENT

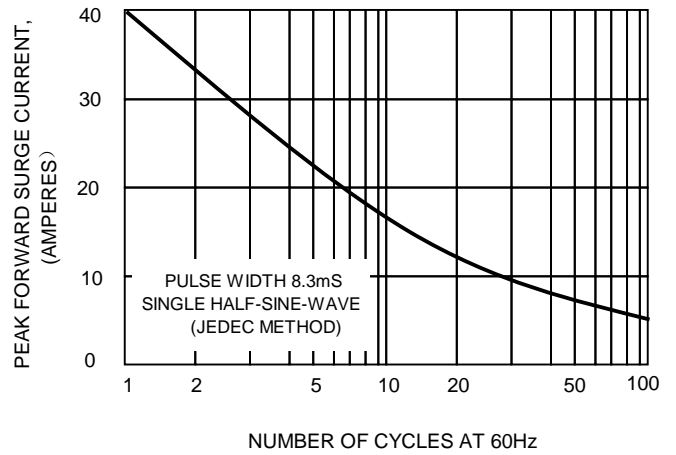


FIG.3 - TYPICAL JUNCTION CAPACITANCE

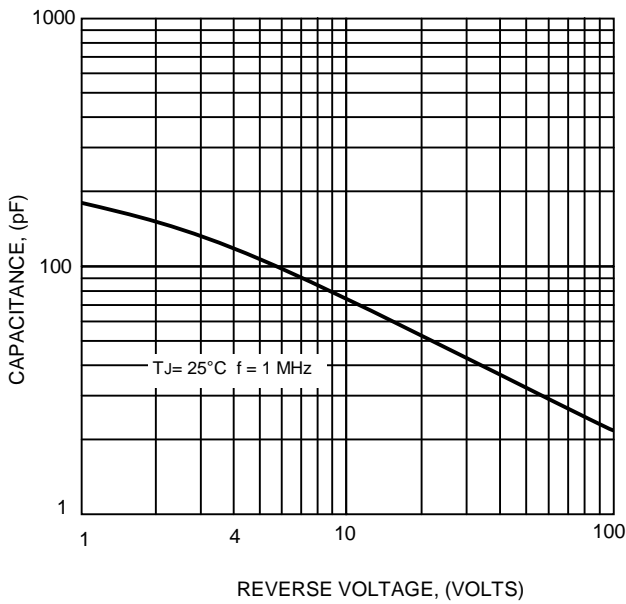


FIG.4-TYPICAL FORWARD CHARACTERISTICS

